

<b>FORM PTO-1449</b>  <b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>  (Use several sheets if necessary)	ATTY. DOCKET NO. <b>200310842-1</b>	APPLICATION NO.	CONFIRMATION NO.
	APPLICANT <b>P t r J. Fricke t al.</b>		
	FILING DATE <b>02-04-2004</b>	GROUP	

## REFERENCE DESIGNATION

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
ON	1A	20030189851A	10-09-2003	Brandenberger et al.	
	1B	20030185048A	10-02-2003	Fricke et al.	
	1C	20030178693A	09-25-2003	Bhattacharyya et al.	
	1D	20030161175A	08-28-2003	Fricke et al.	
	1E	20030151948A	08-14-2003	Bhattacharyya	
	1F	20030081446A	05-01-2003	Fricke et al.	
	1G	20030072126A	04-17-2003	Bhattacharyya	
	1H	6,549,447-B	04-15-2003	Fricke et al.	
	1I	20030042534A	03-06-2003	Bhattacharyya	
	1J	20020028541A	03-07-2002	Lee et al.	
ON	1K	6,344,373-B	02-05-2002	Bhattacharyya et al.	

## FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE OR APPLICANT	Pages/Columns/Lines Where Relevant Passages/Figures Appear	Check if Translation attached
	1L				
	1M				
	1N				
	1O				
	1P				

## OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

ON	1Q	DIMARIA et al., "Enhanced conduction and minimized charge trapping in electrically alterable read-only memories using off-stoichiometric silicon dioxide films" J. Appl. Phys. 55 (8), 15 Apr 1984, pp. 3000-3019
ON	1R	DIMARIA et al., "Enhanced storage dynamic cell using composite silicon-rich SiO <sub>2</sub> and thermal SiO <sub>2</sub> layers" IBM Tech. Discl. Bull., Mar. 1984, pp. 5380-5383
ON	1S	DIMARIA et al., "Use of composite silicon-rich SiO <sub>2</sub> /2/ and SiO <sub>2</sub> /2/ layers or off-stoichiometric CVD SiO <sub>2</sub> /2/ layers for improvement of poly 1 to poly 2 dielectric" IBM Tech. Discl. Bull., May 1983, p. 6417

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EXAMINER INITIAL		DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
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	1B	5,617,351-B	04-01-1997	Bertin et al.	
	1C	5,481,128-B	01-02-1996	Hong	
	1D	5,468,663-B	11-21-1995	Bertin et al.	
	1E	5,451,535-B	09-19-1995	Chan et al.	
	1F	5,331,189-B	07-19-1994	Chan et al.	
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ON	1R	DIMARIA et al., "Electrically-Alterable Memory Using A Dual Electron Injector Structure," Electron Dev. Let., EDL-1 (9), Sept. 1980, pp. 179-181
ON	1S	DIMARIA et al. "Two carrier dual injector structur," IBM Tech. Discl. Bull., Aug 1980, pp. 1277-1279

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EXAMINER INITIAL		DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
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ON	1Q	DIMARIA et al. "Dual electron injector structure" Appl. Phys. Lett. 37(1), 1 Jul. 1980, pp. 61-64
ON	1R	DIMARIA et al. "High current injection into SiO <sub>2</sub> from Si rich SiO <sub>2</sub> films and experimental applications," J. Appl. Phys., 51(5), May 1980, pp. 2722-2735
ON	1S	DIMARIA et al., "High current injection into SiO <sub>2</sub> using Si-rich SiO <sub>2</sub> films and experimental applications," in "The Physics of MOS Insulators" (G. Lucovsky et al., Eds.) Pergamon Press, New York, 1980

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